Application No.: 09/295,607

Art Unit: 2811

## Attorney l BEST AVAILABLE CO

ket No.: 740756-1961 Page 2

(Amended) The device of claim 7 wherein said insulating film comprising 34. aluminum nitride has a thickness of 100 Å to 5000 Å.

35. (Amended) The device of claim 8 wherein said insulating film has a thickness of 100 Å to 5000 Å.

G**5** 

112 let

- 39. (Amended) The display of claim 21 wherein said aluminum nitride insulating film has a thickness of 100 Å to 5000 Å.
- (Amended) The device of claim 2 wherein said channel formation region is 43. crystallized by laser irradiation through a layer comprising at least one of silicon oxide and silicon nitride on said channel formation region.
- (Amended) The device of claim 3 wherein said channel formation region is 44. crystallized by laser irradiation through a layer comprising at least one of silicon oxide and silicon nitride on said channel formation region.
- (Amended) The device/of claim 6 wherein said channel formation region is 45. crystallized by laser irradiation through a layer comprising at least one of silicon oxide and silicon nitride on said channel formation region.
- (Amended) The device of claim 7 wherein said channel formation region is 46. crystallized by laser irradiation through a layer comprising at least one of silicon oxide and 112 st silicon nitride on said channel formation region.
- (Amended) The device of claim 8 wherein said channel formation region is 47. crystallized by laser irradiation through a layer comprising at least one of silicon oxide and silicon nitride on said charnel formation region.
- (Amended) The device of claim 19 wherein said channel formation region is 48. crystallized by laser irradiation through a layer comprising at least one of silicon oxide and 112 lot silicon nitride on said channel formation region.
- (Andended) The device of claim 20 wherein said channel formation region is 49. crystallized by laser irradiation through a layer comprising at least one of silicon oxide and 112 lot silicon nitride of said channel formation region.
- (Amended) The device of claim 21 wherein said channel formation region is 50. crystallized by laser irradiation through a layer comprising at least one of silicon oxide and 112 lat silicon nitride on said channel formation region.